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**(71) Applicant (for all designated States except US): KONINKLIJKE PHILIPS ELECTRONICS N.V. [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).**

**(72) Inventor; and**

**(75) Inventor/Applicant (for US only):** HIJZEN, Erwin, A. [NL/BE]; c/o Philips Intellectual Property & Standards, Cross Oak Lane, Redhill, Surrey RH1 5HA (GB).

(74) **Agent: SHARROCK, Daniel, J.**; Philips Intellectual Property & Standards, Cross Oak Lane, Redhill, Surrey RH1 5HA (GB).

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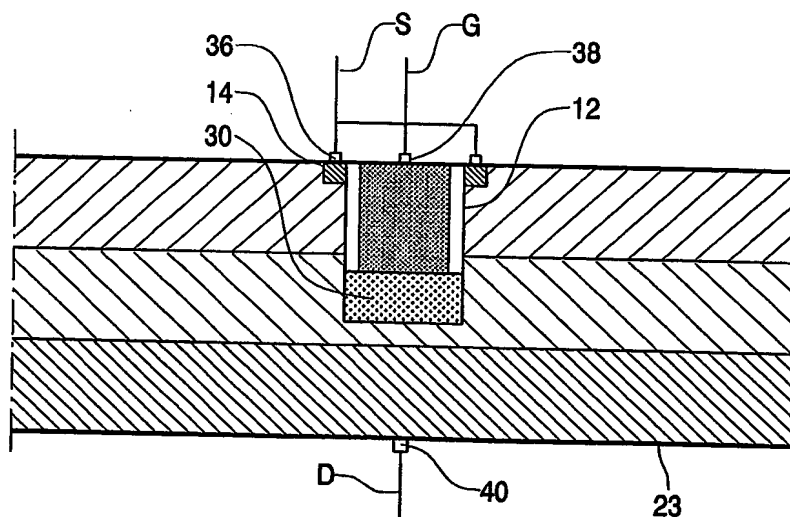
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**(54) Title:** METHOD OF MANUFACTURE OF A TRENCH-GATE SEMICONDUCTOR DEVICE



**(57) Abstract:** A method of making a trench MOSFET includes forming a layer of porous silicon (26) at the bottom of a trench and then oxidizing the layer of porous silicon (26) to form a plug (30) at the bottom of the trench. This forms a thick oxide plug at the bottom of the trench thereby reducing capacitance between gate and drain.

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